# 2N3715 & 2N3716



### **NPN High Power Silicon Transistor**

Rev. V2

#### **Features**

- Available in JAN, JANTX, JANTXV per MIL-PRF-19500/408
- TO-3 (TO-204AA) Package



#### **Electrical Characteristics**

Parameter	Test Conditions	Symbol	Units	Min.	Max.			
Off Characteristics								
Collector - Emitter Breakdown Voltage	$I_C$ = 10 mAdc, 2N3715 $I_C$ = 10 mAdc, 2N3716	V <sub>(BR)CEO</sub>	Vdc	60 80	_			
Collector - Base Cutoff Current	V <sub>CE</sub> = 60 Vdc, 2N3715 V <sub>CE</sub> = 80 Vdc, 2N3716	I <sub>CEO</sub>	μAdc	_	10 10			
Emitter - Base Cutoff Current	V <sub>EB</sub> = 7 Vdc	I <sub>EBO</sub>	mAdc	_	1			
Collector - Emitter Cutoff Current	$V_{CE}$ = 60 Vdc, $V_{BE}$ = 1.5 Vdc, 2N3715 $V_{CE}$ = 80 Vdc, $V_{BE}$ = 1.5 Vdc, 2N3716	I <sub>CEX</sub>	μAdc	_	10 10			
Collector - Emitter Cutoff Current	$V_{CE}$ = 50 Vdc, 2N3715 $V_{CE}$ = 70 Vdc, 2N3716	I <sub>CEO</sub>	μAdc	_	10 10			
On Characteristics <sup>1</sup>								
Forward Current Transfer Ratio	$I_C$ = 1 Adc, $V_{CE}$ = 2 Vdc $I_C$ = 3 Adc, $V_{CE}$ = 2 Vdc $I_C$ = 5 Adc, $V_{CE}$ = 2 Vdc $I_C$ = 10 Adc, $V_{CE}$ = 4 Vdc	H <sub>FE</sub>	-	50 30 10 5	150 120 —			
Collector - Emitter Saturation Voltage	$I_C = 5 \text{ Adc}, I_B = 0.5 \text{ Adc}$ $I_C = 10 \text{ Adc}, I_B = 2.0 \text{ Adc}$	V <sub>CE(SAT)</sub>	Vdc	_	1.0 2.5			
Emitter - Base Saturation Voltage	$I_C = 5 \text{ Adc}, I_B = 0.5 \text{ Vdc}$ $I_C = 10 \text{ Adc}, I_B = 2.0 \text{ Vdc}$	V <sub>BE(SAT)</sub>	Vdc	_	1.5 3.0			
Dynamic Characteristics								
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio	I <sub>C</sub> = 4 Adc, V <sub>CE</sub> = 4 Vdc, f = 100 kHz	H <sub>FE</sub>		4	20			
Small-Signal Short-Circuit Forward Current Transfer Ratio	I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1 kHz	H <sub>FE</sub>		30	300			
Output Capacitance	V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, 100 kHz ≤ f ≤ 1 MHz	Сово	pF	_	500			

#### Safe Operating Area

<sup>1.</sup> Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤2.0%.



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#### **Absolute Maximum Ratings**

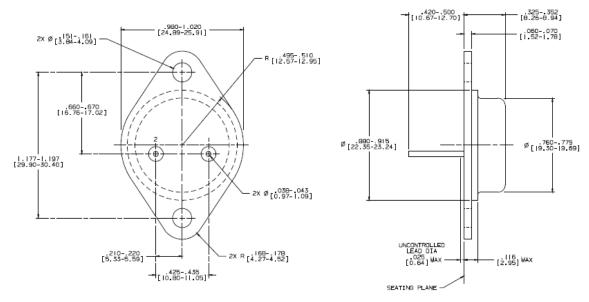
Ratings	Symbol	Value
Collector - Emitter Voltage 2N3715 2N3716	V <sub>CEO</sub>	60 Vdc 80 Vdc
Collector - Base Voltage 2N3715 2N3716	V <sub>CBO</sub>	80 Vdc 100 Vdc
Emitter - Base Voltage	$V_{EBO}$	7 Vdc
Base Current	I <sub>B</sub>	4 Vdc
Collector Current	Ic	10 Adc
Total Power Dissipation  @ $T_A = 25^{\circ}C^2$ @ $T_A = 25^{\circ}C$	P <sub>T</sub>	5 W 117 W
Operating & Storage Temperature Range	T <sub>OP</sub> , T <sub>STG</sub>	-65°C to +200°C

<sup>2.</sup> Derate linearly @ 28.57 mW /  $^{\circ}$ C for T<sub>A</sub> = 25  $^{\circ}$ C

#### **Thermal Characteristics**

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5°C/W

## **Outline Drawing**



#### NOTES:

- NOTES:

  1. STANDARD HEADER TYPE SOLID BASE.

  2. STANDARD LEAD FINISHIPER WIL-W-38510 TYPE X OR EQUIVALENT.

  3. LEAD NOT BENT GREATER THAN 15\*

  4. DIMENSIONS BASED ON JEDEC STANDARD TO-3 PUBLICATION 95, PA

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